

79. (New) The method according to claim 78 wherein said semiconductor film comprises amorphous silicon.

80. (New) The method according to claim 78 wherein said semiconductor film is crystallized before the irradiation with the laser light.

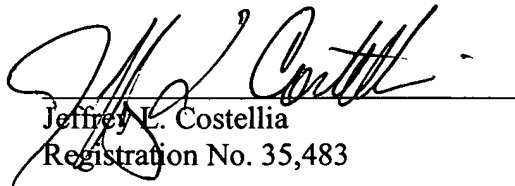
81. (New) The method according to claim 78 wherein said semiconductor film is crystallized before the irradiation with the laser light wherein the crystallization of the semiconductor film is promoted by adding a metal element thereto.

REMARKS

Applicants hereby elect without traverse Species 2, a metal amorphous semiconductor film, example (claims 6-8). In addition, claims 78-81 are added to further recite the invention to which applicants are entitled. Specifically, claims 78-81 are generic to Species 1 and 2.

Consideration and allowance of the instant application are now respectfully requested.

Respectfully submitted,


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